

/ Descriptions

SOT23-3

P- CHANNEL MOSFET in a SOT23-3 Plastic Package.

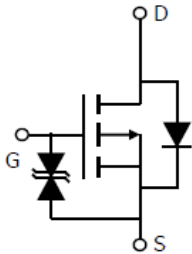
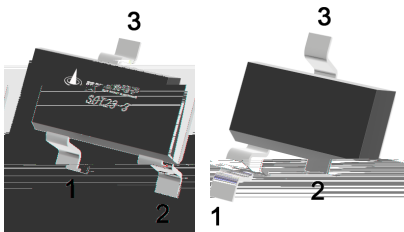
/ Features $R_{DS(ON)} < 41\text{ m}\Omega, V_{GS} = -4.5\text{V}$ $R_{DS(ON)} < 53\text{ m}\Omega, V_{GS} = -2.5\text{V}$

Qualified to AEC-Q101 Standards for High Reliability,

HF Product.

/ Applications

Load switch Battery protection, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit**/ Pinning**

PIN1 G

PIN 2 S

PIN 3 D

/ Marking

Marking

AFQ

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	8	V
Drain Current-Continuous @ $T_C = 25^\circ\text{C}$	I_D	-4	A
Drain Current-Pulsed Note1 @ $T_C = 25^\circ\text{C}$	I_{DM}	-30	A
Maximum Power Dissipation	P_D	1.5	W
Storage Temperature Range	T_{STG}	-55 to +150	C
Operating Junction Temperature Range	T_J	-55 to +150	C
Thermal Resistance, Junction-to-Ambient Note2	$R_{\theta JA}$	100	C/W

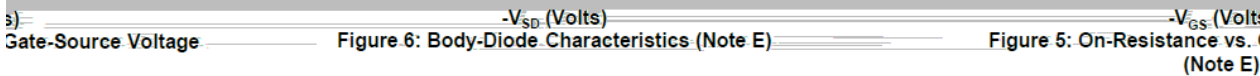
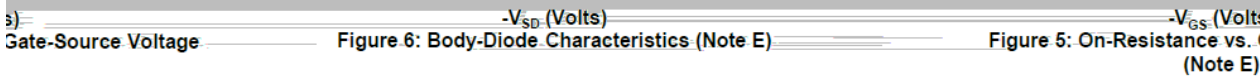
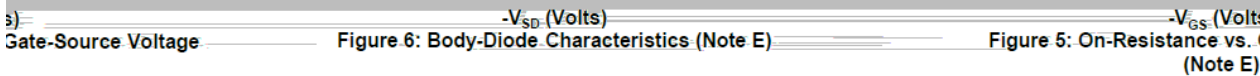
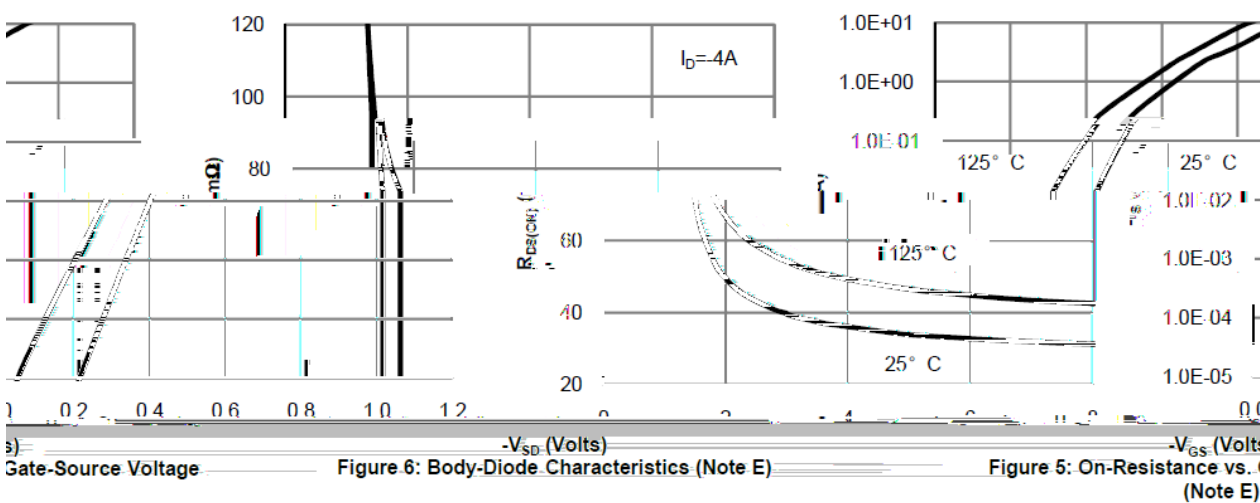
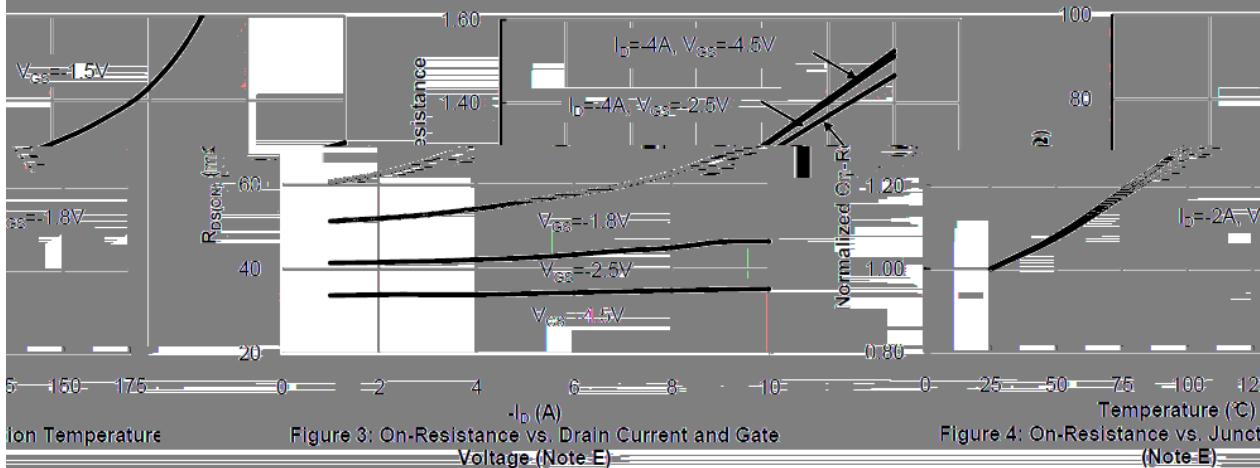
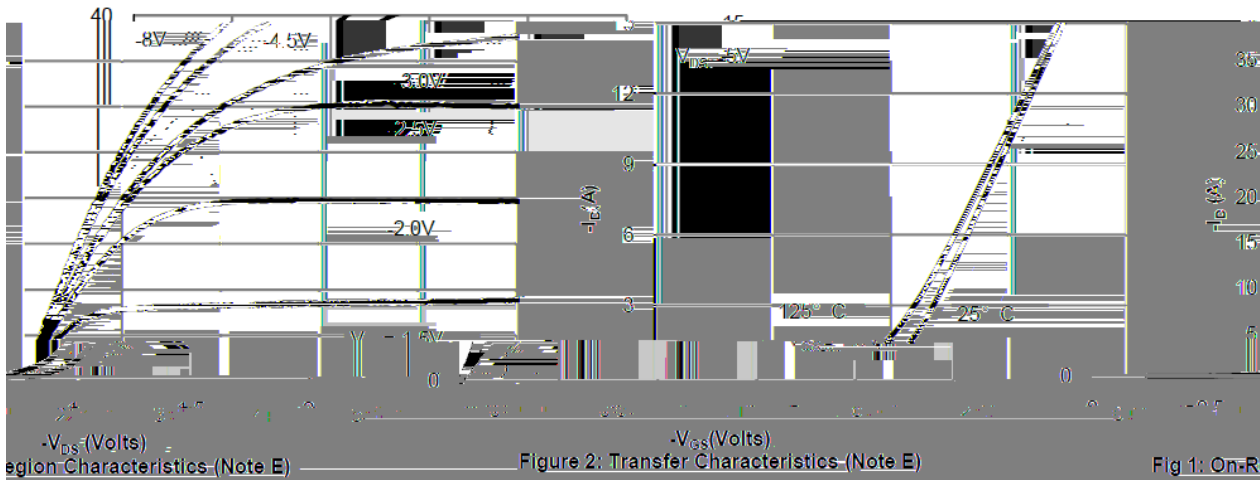
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$B_{V_{DS}}$	$V_{GS}=0V$ $I_{DS}=-250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V$ $V_{GS}=0V$			-1	μA
Gate-Body Leakage	I_{GSS}	$V_{GS}=\pm 8V$ $V_{DS}=0V$			10	μA
Gate Threshold Voltage	V_{TH}	$V_{DS}=V_{GS}$ $I_{DS}=-250\mu A$	-0.3	-0.6	-0.9	V
Drain-Source On-State Resistance	R_{DS}	$V_{GS}=-4.5V$ $I_{DS}=-4A$		35	41	$m\Omega$
		$V_{GS}=-2.5V$ $I_{DS}=-4A$		45	53	
Input Capacitance	C_{iss}	$V_{DS}=-10V$ $V_{GS}=0V$ $f=1MHz$		750		pF
Output Capacitance	C_{oss}			110		
Reverse Transfer Capacitance	C_{rss}			80		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-10V$ $V_{GS}=-4.5V$ $R_G=3$ $R_L=2.5$		15.6		ns
Rise Time	t_r			11.2		
Turn-Off Delay Time	$t_{d(off)}$			23.1		
Fall Time	t_f			32.7		
Total Gate Charge at 10V	Q_g	$V_{DS}=-10V$ $I_{DS}=-4A$ $V_{GS}=-4.5V$		10		
Gate to Source Gate Charge	Q_{gs}			1.5		
Gate to Drain "Miller" Charge	Q_{gd}			2.2		
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_{DS}=-1A$		-0.7		V

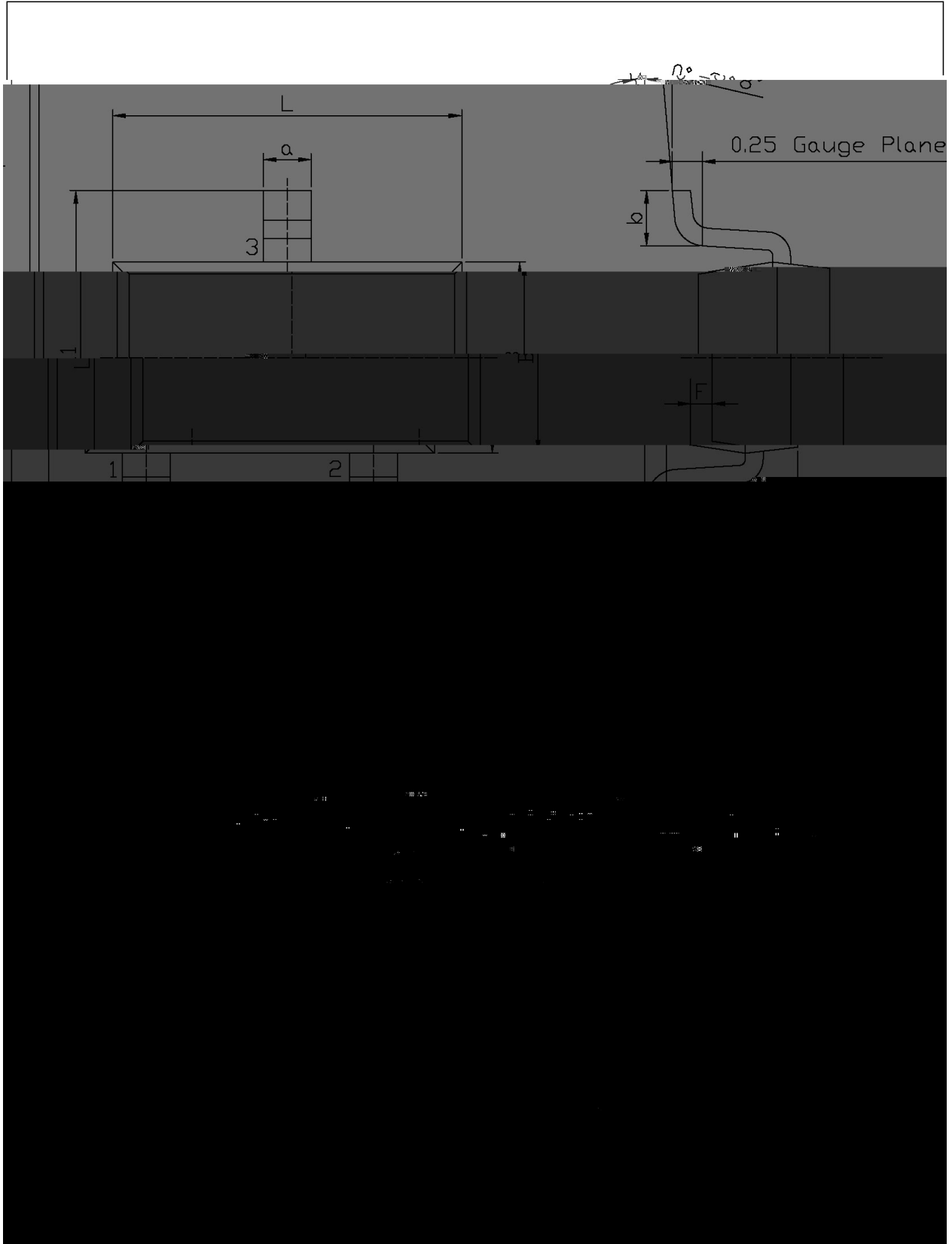
Notes:

1. Pulse Test: Pulse Width 300 μs , Duty Cycle 2%.
2. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 in still air.

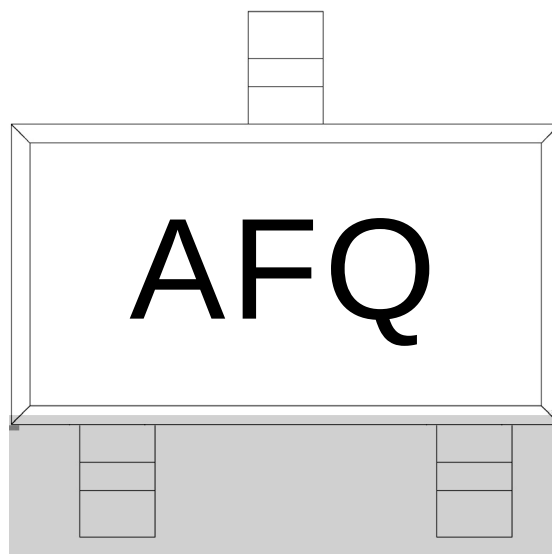
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



AF:

Note:

Q: Automobile halogen-free product Code

AF Product Type

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- 1

150 200

60 120sec;

1.Preheating:150~200 , Time:60~120sec.
- 2

255 5

5 0.5sec;

2.Peak Temp.:255 5 , Duration:5 0.5sec.
- 3

2 10

/sec.

3. Cooling Speed: 2~10 /sec.